



# MMBTH10

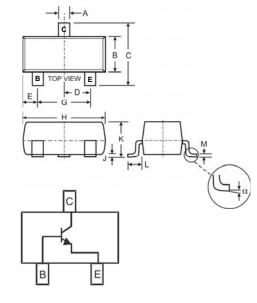
## NPN SURFACE MOUNT VHF/UHF TRANSISTOR

#### **Features**

- Designed for VHF/UHF Amplifier Applications and High Output VHF Oscillators
- High Current Gain Bandwidth Product
- Ideal for Mixer and RF Amplifier Applications with collector currents in the 100µA 30 mA Range
- Lead Free/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: K3H, K3Y; See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23									
Dim	Min	Max							
Α	0.37	0.51							
в	1.20	1.40							
С	2.30	2.50							
D	0.89	1.03							
Е	0.45	0.60							
G	1.78	2.05							
н	2.80	3.00							
J	0.013	0.10							
к	0.903	1.10							
L	0.45	0.61							
М	0.085	0.180							
α	0°	8°							
All Din	All Dimensions in mm								

## **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V <sub>CBO</sub>	30	V		
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V		
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	V		
Collector Current - Continuous (Note 1)	Ι <sub>C</sub>	50	mA		
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW		
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>0JA</sub>	417	°C/W		
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C		

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition					
OFF CHARACTERISTICS (Note 2)										
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	25		V	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	30	_	V	$I_{\rm C} = 100 \mu {\rm A}, \ I_{\rm E} = 0$					
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	3.0		V	$I_{E} = 10 \mu A, I_{C} = 0$					
Collector Cutoff Current	I <sub>CBO</sub>		100	nA	$V_{CB} = 25V, I_E = 0$					
Emitter Cutoff Current	I <sub>EBO</sub>	_	100	nA	$V_{EB} = 2V, I_{C} = 0$					
ON CHARACTERISTICS (Note 2)										
DC Current Gain	h <sub>FE</sub>	60	_	_	$I_{C} = 4mA, V_{CE} = 10.0V$					
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.5	V	$I_{C} = 4mA, I_{B} = 400 \mu A$					
Base-Emitter On Voltage	V <sub>BE(SAT)</sub>	_	0.95	V	$I_{C} = 4mA, V_{CE} = 10.0V$					
SMALL SIGNAL CHARACTERISTICS	• •				•					
Current Gain-Bandwidth Product	f⊤	650		MHz	$V_{CE} = 10V$ , f = 100MHz, I <sub>C</sub> = 4mA					
Collector-Base Capacitance	C <sub>CB</sub>	_	0.7	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$					
Collector-Base Feedback Capacitance	C <sub>RB</sub>	_	0.65	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$					
Collector-Base Time Constant	Rb'Cc	_	9	ps	$V_{CB} = 10V, f = 31.8MHz, I_{C} = 4mA$					

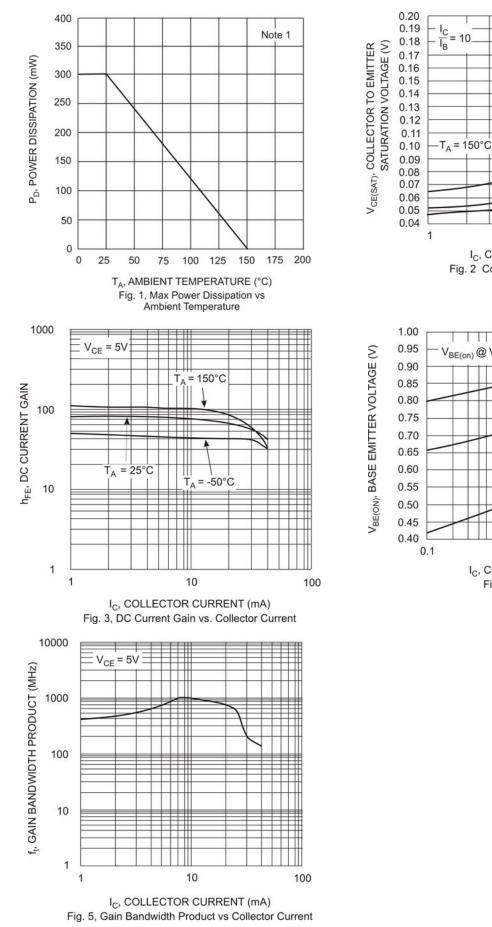
Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, pad layout as shown on Diodes Inc. suggested pad layout

document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. Short duration pulse test used to minimize self-heating effect.

3. No purposefully added lead.





= 25°C

10

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Fig. 2 Collector Emitter Saturation Voltage

vs. Collector Current

= -50°C 111

T<sub>A</sub> = 150°C

10

= 25°C T<sub>A</sub>

I<sub>C</sub>, COLLECTOR CURRENT (mA)

Fig. 4 Base Emitter Voltage vs. Collector Current

1

V<sub>BE(on)</sub> @ V<sub>CE</sub> = 5V

 $T_A = -50^{\circ}C$ 

1000

1000

TA

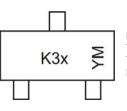


#### Ordering Information (Note 4)

Device	Packaging	Shipping
MMBTH10-7-F	SOT-23	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## Marking Information



 $\begin{array}{l} \mathsf{K3x} = \mathsf{Product Type Marking Code, e.g. K3H} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year ex: N} = 2002 \\ \mathsf{M} = \mathsf{Month ex: 9} = \mathsf{September} \end{array}$ 

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	lov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

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